



Product Overview

MBR830MFS: 8 A, 30 V Schottky Diode in SO-8FL

For complete documentation, see the data sheet

Product Description

8 A, 30 V Schottky Diode in SO-8FL

Features

- Low Power Loss / High Efficiency
- New Package Provides Capability of Inspection and Probe After Board Mounting
- Guardring for Stress Protection
- Low Forward Voltage
- 150°C Operating Junction Temperature
- Wettable Flacks Option Available
- NRVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free and Halide-Free Devices

Applications

- Automotive engine control modules
- Automotive infotainment modules
- Automotive LED headlighting
- Compact notebook adapters
- High frequency SMPS

End Products

- Automotive

Part Electrical Specifications

Product	Compliance	Status	Configuration	V_{RRM} Min (V)	V_F Max (V)	I_{RM} Max (uA)	$I_{O(rec)}$ Max (A)	I_{FSM} Max (A)	t_r Max (ns)	C_j Max (pF)	Package Type
MBR830MFST1G	AEC Qualified Pb-free Halide free	Active	Single	30	0.7	200	8	150			SO-8FL / DFN-5
MBR830MFST3G	AEC Qualified Pb-free Halide free	Active	Single	30	0.7	200	8	150			SO-8FL / DFN-5
NRVB830MFST1G	AEC Qualified PPAP Capable Pb-free Halide free	Active	Single	30	0.7	200	8	150			SO-8FL / DFN-5
NRVB830MFST3G	AEC Qualified PPAP Capable Pb-free Halide free	Active	Single	30	0.7	200	8	150			SO-8FL / DFN-5

For more information please contact your local sales support at www.onsemi.com

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